

Features

- Bi-directional crowbar transient voltage protection
- High surge capability
- High off-state impedance
- Low leakage current
- Low on-state voltage
- Short-circuit failure mode
- Ultra Low Capacitance (Typ:55.0pF)



DO-214AA(SMB)

Main Application

JKSEMI's thyristor surge protector devices are designed help protect sensitive telecommunication equipment from the hazards caused by lighning ,power contact, and power induction. These devices enable equipment to comply with various regulatory requirements including GR 1089,ITU K.20,K.21and K.45,IEC 60950,UL 60950,and TIA-968-A(formerly known as FCC Part 68).

Typical application including:

- Central office switching equipment. Analog and digital linecards(xDSL,T1/E1,ISDN.....)
- Customer Premises Equipment (CPE) such as phones, fax machines, modems, POS terminals, PBX systems and caller ID adjunct boxes.
- Primary protection modules including Main Distribution Frames (MDF), building entrance equipment and station protection modules.
- Access network equipment such as remote terminals, line repeaters, multiplexers, cross-connects, WAN equipment, Network Interface Devices (NID).
- Data lines and security systems.
- CATV line amplifiers and power inserters.
- Sprinkler systems.

Electrcal Parameters (Tamb=25°C)

Part Number	VDRM Min.	IDRM Max.	VBO Max.	Іво Мах.	VT Max.	IT Max.	Со Тур.	`Ін Min.
	V	uA	V	mA	V	A	pF	mA
PE06SB	6	2	15	800	3	2.2	55	30



Part Number	VDRM Min.	IDRM Max.	VBO Max.	Іво Мах.	VT Max.	IT Max.	Co Max.	`Ін Min.
	V	uA	V	mA	V	A	pF	mA

Eletrical Characteristics

VDRM	Stand-off voltage, is measured at IDRM	Ін	Holding current.
VBO	Breakover voltage, is measured at 100V/μs.	Іво	Breadover current.
Со	Off-state capacitance ismeasured in VDC=2V@1MHZ.	lτ	ON-state current
IDRM	Leakage current,is measured at VDRM.	VT	On-state voltage.

Part Numbering System

$$\underbrace{PE}_{(A)} \quad \underbrace{XX} \quad \underbrace{S} \quad \underbrace{B}_{(C)} \quad \underbrace{(D)}$$

- (A) Jksemi's Semiconductor Surge Arrester;
- (B) Series:0060etc.
- (C) Package:DO-214AA(SMB)
- (D) Rating Sure Voltage:B:4KV(10/700µs)

Electrical Characteristics Curves

Figure 1 V-I Characteristics

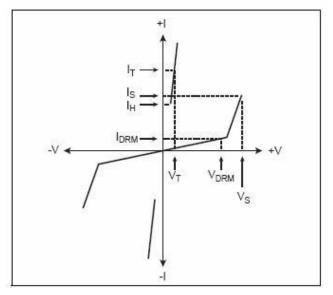


Figure 3 Normalized V_S Change versus Junction Temperature

Figure 2 tr x td Pulse Wave-form

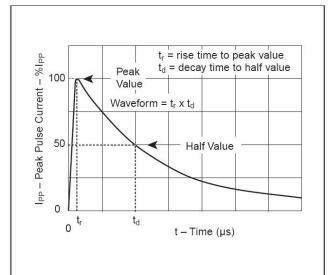
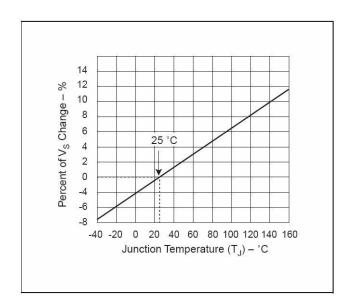
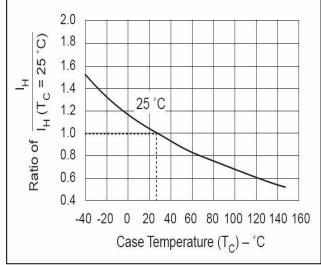


Figure 4 Normalized DC Holding Current

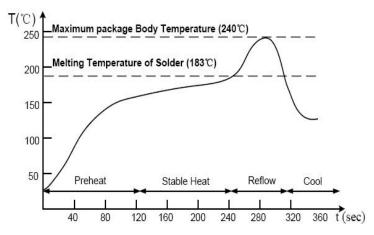




Thermal Considerations

Package DO-214AA/SMB	Symbol	Parameter	Value	Unit
	TJ	Operating Junction Temperature	-40 to +150	${\mathbb C}$
	Ts	Storage Temperature Range	-40 to +150	$^{\circ}$
	R _Ө ЈА	Junction to Ambient on printed circuit	90	°C/W

Solder Reflow Recommendations

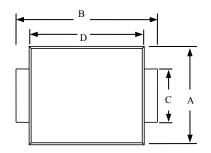


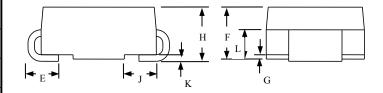
- Recommended reflow methods: IR, vapor phase oven, hot air oven, wave solder.
- The device can be exposed to a maximum temperature of 265°C for 10 seconds.
- Devices can be cleaned using standard industry methods and solvents.

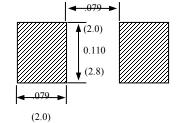
Notes: If reflow temperatures exceed the recommended profile, devices may not meet the performance requirements.

Product Dimensions

Dimension	Inc	hes	Millimeters		
Dimension	Min	Max	Min	Max	
A	0.134	0.155	3.40	3.94	
В	0.205	0.22	5.21	5.59	
С	0.075	0.083	1.90	2.11	
D	0.166	0.185	4.22	4.70	
Е	0.036	0.056	0.91	1.42	
F	0.073	0.087	1.85	2.2	
G	0.002	0.008	0.05	0.20	
Н	0.077	0.094	1.95	2.40	
J	0.043	0.053	1.09	1.35	
K	0.008	0.014	0.20	0.35	
L	0.039	0.049	0.99	1.24	







Summary of Packing Options

Package Type	Description	Packing	Industry	
rackage Type	Description	Quantity	Standard	
DO-214AA				
	Embossed Carrier Reel Pack	3000PCS	EIA-481-D	